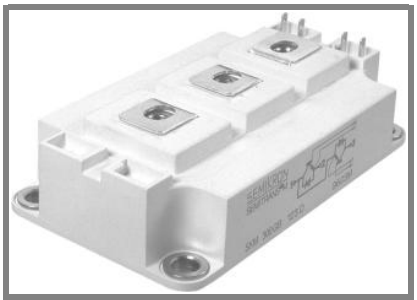
SKM 400GB125D



SEMITRANS® 3

Ultra Fast IGBT Modules

SKM 400GB125D

SKM 400GAL125D

SKM 400GAR125D

Features

- Low inductance case
- Short tail current with low temperature dependence
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- Fast & soft inverse CAL diodes
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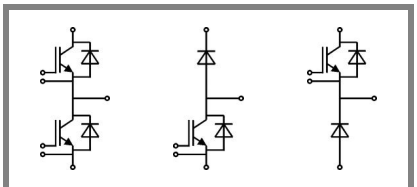
- Large clearance (13 mm) and creepage distances (20 mm)

Typical Applications*

- Switched mode power supplies at f_{sw} >20kHz
- Resonant inverters up to 100 kHz
- Inductive heating
- Electronic welders at f_{sw} > 20 kHz

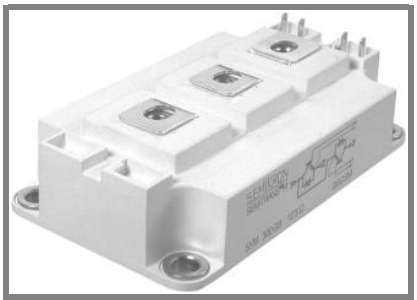


GB GAL GAR

Absolute Maximum Ratings			T_c = 25 °C, unless otherwise specified	
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	T_j = 150 °C	T_{case} = 25 °C	400	A
		T_{case} = 80 °C	300	A
I_{CRM}	I_{CRM}=2xI_{Cnom}		600	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 600 V; $V_{GE} \leq$ 20 V; V_{CES} < 1200 V	T_j = 125 °C	10	µs
Inverse Diode				
I_F	T_j = 150 °C	T_{case} = 25 °C	390	A
		T_{case} = 80 °C	260	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		600	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	2880	A
Freewheeling Diode				
I_F	T_j = 150 °C	T_{case} = 25 °C	390	A
		T_{case} = 80 °C	260	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		600	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	2880	A
Module				
$I_{t(RMS)}$			500	A
T_{vj}			- 40...+ 150	°C
T_{stg}			- 40...+ 125	°C
V_{isol}	AC, 1 min.		4000	V

Characteristics			T_c = 25 °C, unless otherwise specified			
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 12 mA		4,5	5,5	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C		0,15	0,45	mA
V_{CE0}		T_j = 25 °C		1,4		V
		T_j = 125 °C		1,7		V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		6,3		mΩ
		T_j = 125°C		7,6		mΩ
$V_{CE(sat)}$	I_{Cnom} = 300 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		3,3	3,85	V
		T_j = 125°C$_{chiplev.}$		4	4,55	V
C_{ies}				22	30	nF
C_{oes}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		3,3	4	nF
C_{res}				1,2	1,6	nF
Q_G	V_{GE} = 0V - +20V			2650		nC
R_{Gint}	T_j = °C			1,25		Ω
$t_{d(on)}$	R_{Gon} = 2 Ω	V_{CC} = 600V		70		ns
t_r		I_C= 300A		50		ns
E_{on}		T_j = 125 °C		17		mJ
$t_{d(off)}$	R_{Goff} = 2 Ω	V_{GE} = ±15V		500		ns
t_f				32		ns
E_{off}				18		mJ
$R_{th(j-c)}$	per IGBT				0,05	K/W

SKM 400GB125D



SEMITRANS® 3

Ultra Fast IGBT Modules

SKM 400GB125D

SKM 400GAL125D

SKM 400GAR125D

Features

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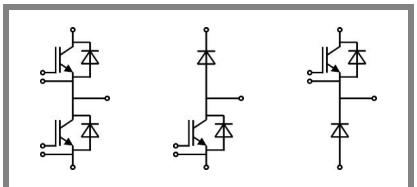
- Resonant inverters up to 100 kHz
- Inductive heating
- Electronic welders at f_{sw} > 20 kHz

Characteristics

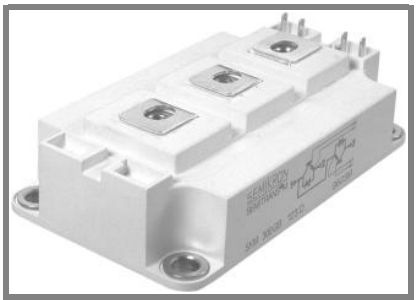
Symbol	Conditions		min.	typ.	max.	Units
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 300 A; V_{GE} = 0 V	T_j = 25 °C$_{chiplev.}$		2	2,5	V
		T_j = 125 °C$_{chiplev.}$		1,8		V
V_{F0}		T_j = 25 °C		1,1	1,2	V
		T_j = 125 °C				V
r_F		T_j = 25 °C		3	4,3	mΩ
		T_j = 125 °C				mΩ
I_{RRM}	I_F = 300 A	T_j = 125 °C		350		A
Q_{rr}	di/dt = 8300 A/µs			45		µC
E_{rr}	V_{GE} = 0 V; V_{CC} = 600 V			16		mJ
$R_{th(j-c)D}$	per diode				0,125	K/W
Freewheeling Diode						
$V_F = V_{EC}$	I_{Fnom} = 300 A; V_{GE} = 0 V	T_j = 25 °C$_{chiplev.}$		2	2,5	V
		T_j = 125 °C$_{chiplev.}$		1,8		V
V_{F0}		T_j = 25 °C		1,1	1,2	V
		T_j = 125 °C				V
r_F		T_j = 25 °C		3	4,3	V
		T_j = 125 °C				V
I_{RRM}	I_F = 300 A	T_j = 125 °C		350		A
Q_{rr}	di/dt = 8300 A/µs			45		µC
E_{rr}	V_{GE} = 0 V; V_{CC} = 600 V			16		mJ
$R_{th(j-c)FD}$	per diode				0,125	K/W
Module						
L_{CE}				15	20	nH
$R_{CC'+EE'}$	res., terminal-chip	T_{case}= 25 °C		0,35		mΩ
		T_{case}= 125 °C		0,5		mΩ
$R_{th(c-s)}$	per module				0,038	K/W
M_s	to heat sink M6		3		5	Nm
M_t	to terminals M6		2,5		5	Nm
w					325	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



GB GAL GAR



SEMITRANS® 3

Ultra Fast IGBT Modules

SKM 400GB125D

SKM 400GAL125D

SKM 400GAR125D

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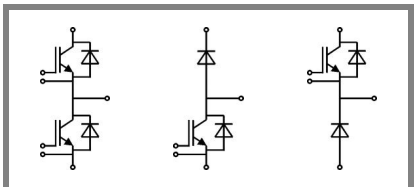

GB GAL GAR

Z_{th} Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	i = 1	36	mk/W
R_i	i = 2	10,5	mk/W
R_i	i = 3	3	mk/W
R_i	i = 4	0,5	mk/W
tau_i	i = 1	0,0744	s
tau_i	i = 2	0,0078	s
tau_i	i = 3	0,0016	s
tau_i	i = 4	0,0002	s
$Z_{th(j-c)D}$			
R_i	i = 1	75	mk/W
R_i	i = 2	38	mk/W
R_i	i = 3	10,6	mk/W
R_i	i = 4	1,4	mk/W
tau_i	i = 1	0,0386	s
tau_i	i = 2	0,0201	s
tau_i	i = 3	0,001	s
tau_i	i = 4	0,003	s

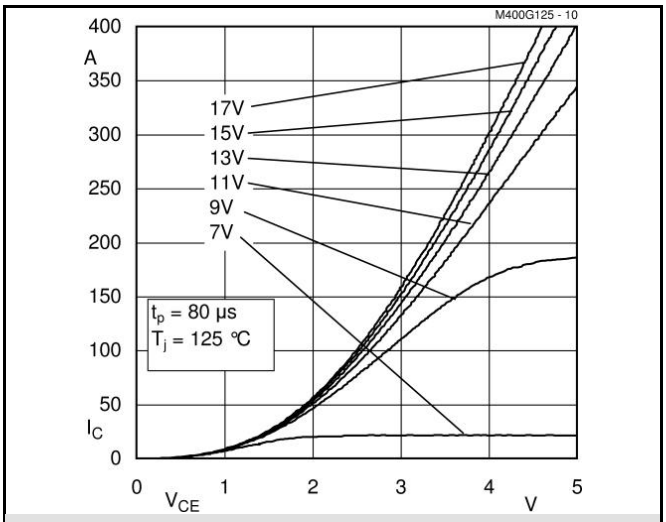

Fig. 1 Typ. output characteristic, inclusive $R_{CC'+ EE'}$

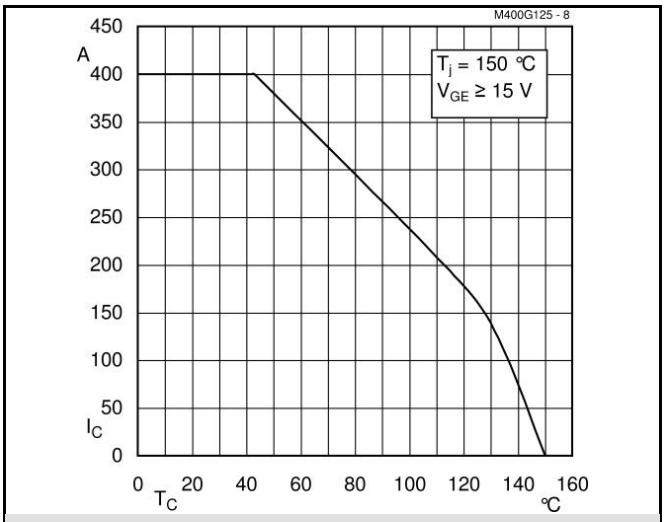

Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

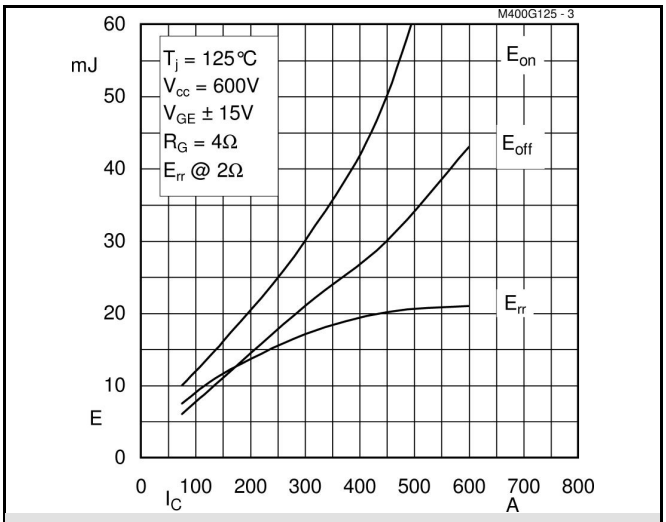

Fig. 3 Typ. turn-on /-off energy = f (I_C)

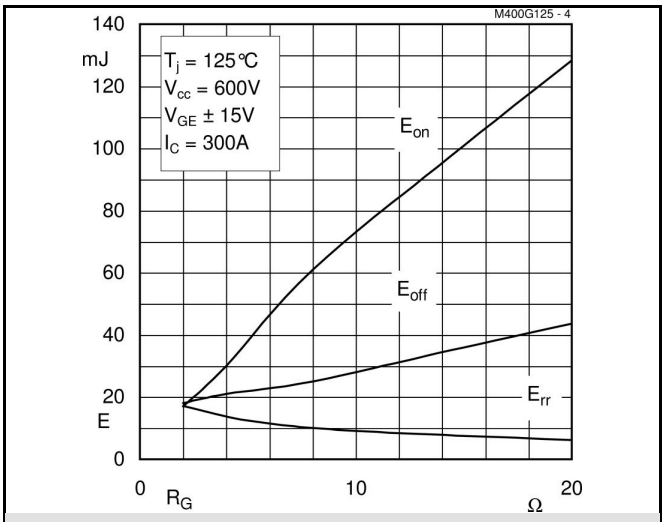

Fig. 4 Typ. turn-on /-off energy = f (R_G)

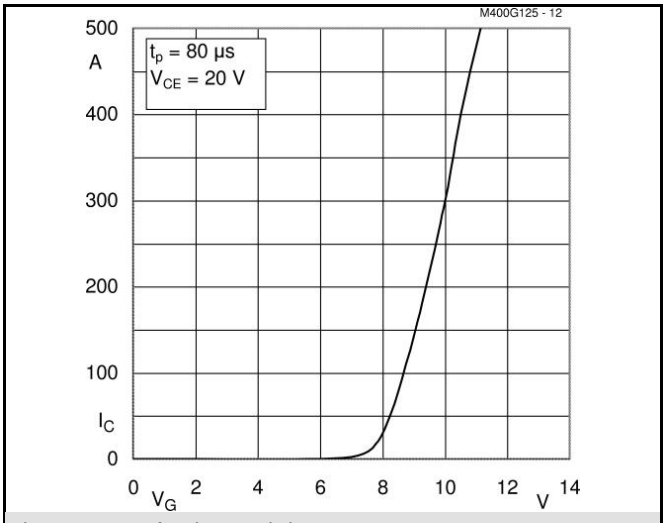

Fig. 5 Typ. transfer characteristic

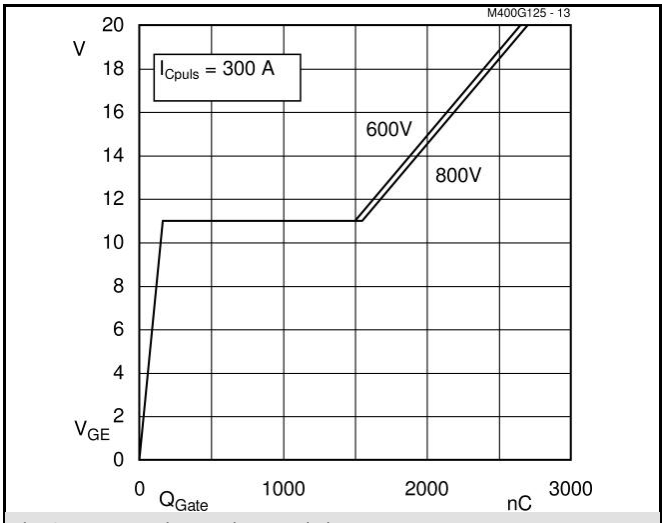

Fig. 6 Typ. gate charge characteristic

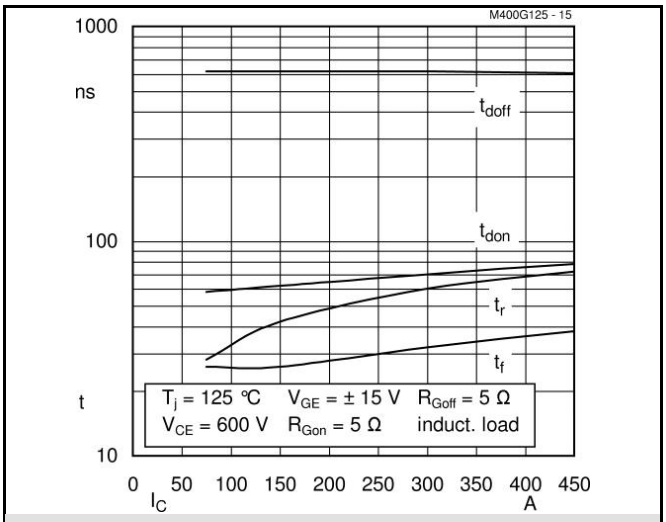

Fig. 7 Typ. switching times vs. I_C

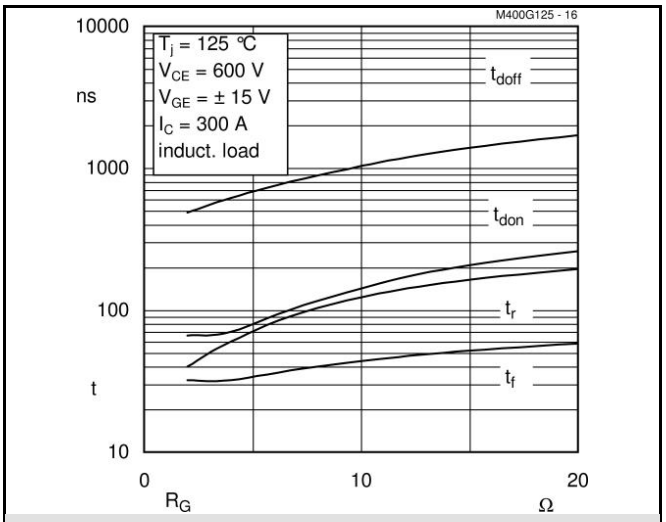

Fig. 8 Typ. switching times vs. gate resistor R_G

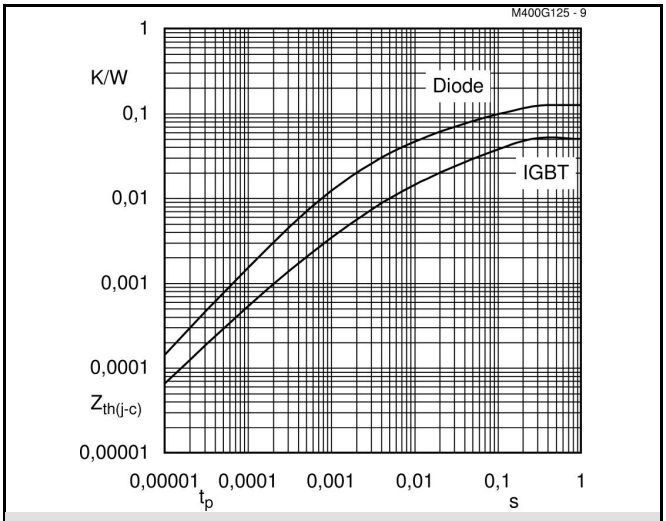

Fig. 9 Transient thermal impedance

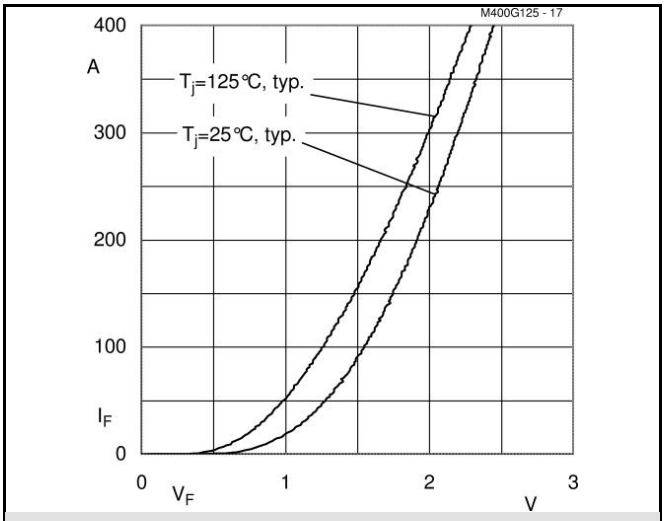

Fig. 10 CAL diode forward characteristic

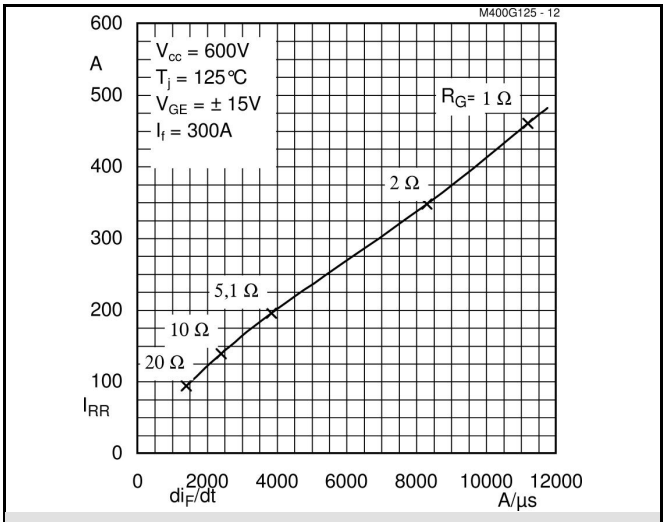

Fig. 11 Typ. CAL diode peak reverse recovery current

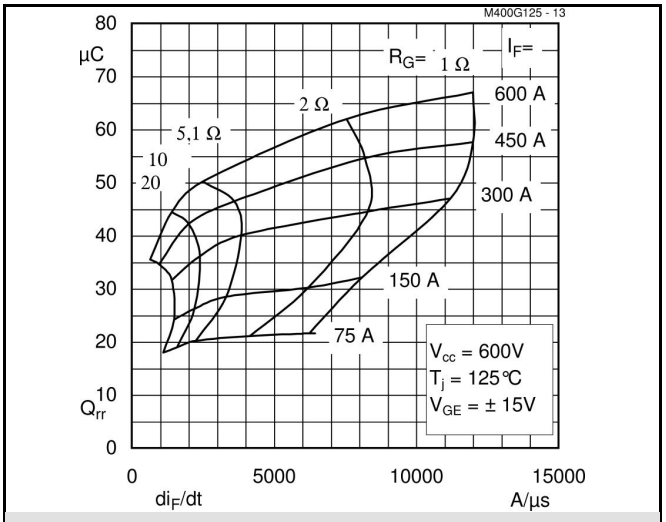

Fig. 12 Typ. CAL diode peak reverse recovery charge

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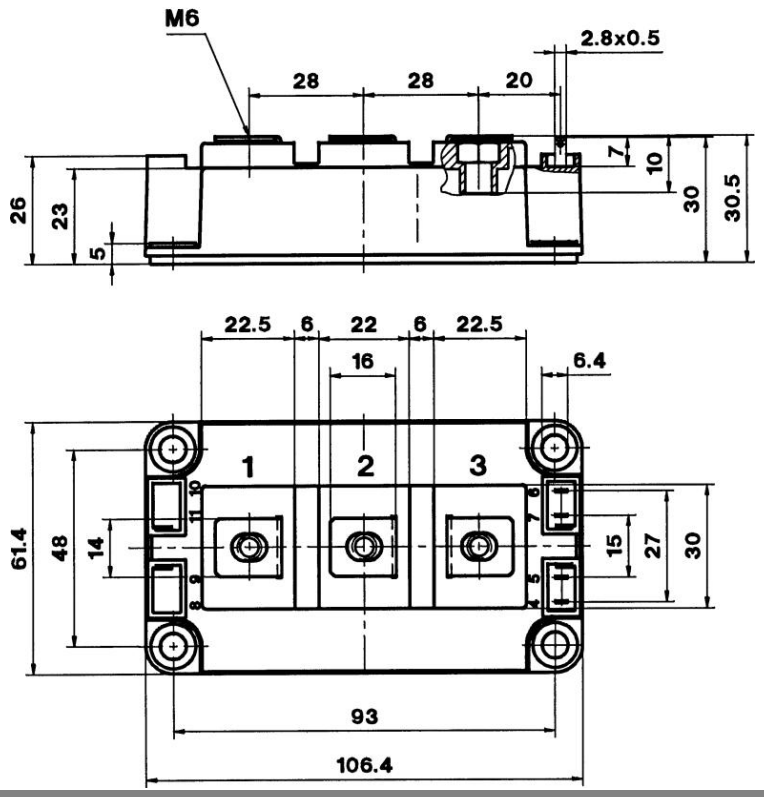
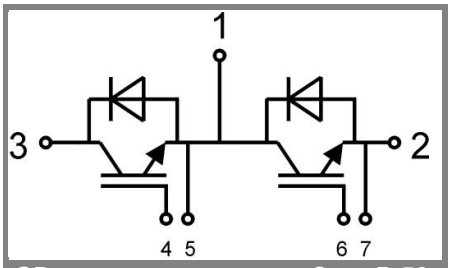
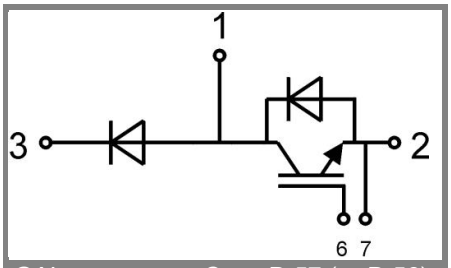


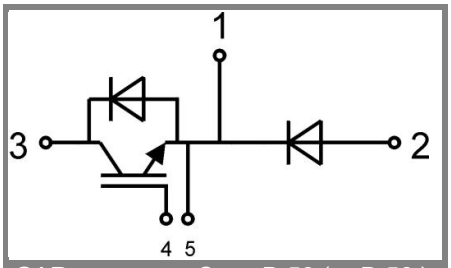
Case D 56



GB Case D 56



GAL Case D 57 (➞ D 56)



GAR Case D 58 (➞ D 56)